

# Ikuo Suemune

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

313  
papers

4,962  
citations

34  
h-index

56  
g-index

327  
ext. papers

5,269  
ext. citations

2.2  
avg, IF

5  
L-index

#	Paper	IF	Citations
313	Microstructures of GaAsN grown on (001) GaAs by metalorganic molecular beam epitaxy <b>2018</b> , 197-200		
312	Optical control of spectral diffusion with single InAs quantum dots in a silver-embedded nanocone. <i>Optics Express</i> , <b>2017</b> , 25, 8073-8084	3.3	2
311	Stable and efficient collection of single photons emitted from a semiconductor quantum dot into a single-mode optical fiber. <i>Applied Physics Express</i> , <b>2016</b> , 9, 032801	2.4	13
310	Superconducting Light-Emitting Diodes. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>2015</b> , 21, 1-11	3.8	8
309	Nonlocal biphoton generation in a Werner state from a single semiconductor quantum dot. <i>Physical Review B</i> , <b>2015</b> , 91,	3.3	3
308	Optical observation of superconducting density of states in luminescence spectra of InAs quantum dots. <i>Physical Review B</i> , <b>2015</b> , 92,	3.3	7
307	Time-resolved measurements of Cooper-pair radiative recombination in InAs quantum dots. <i>Journal of Applied Physics</i> , <b>2015</b> , 118, 073102	2.5	1
306	Ultrahigh quality factor in a metal-embedded semiconductor microdisk cavity. <i>Optics Letters</i> , <b>2015</b> , 40, 5766-9	3	2
305	Subwavelength metallic cavities with high-Q resonance modes. <i>Nanotechnology</i> , <b>2015</b> , 26, 085201	3.4	2
304	Vanishing fine-structure splittings in telecommunication-wavelength quantum dots grown on (111)A surfaces by droplet epitaxy. <i>Physical Review B</i> , <b>2014</b> , 90,	3.3	34
303	Two-photon interference and coherent control of single InAs quantum dot emissions in an Ag-embedded structure. <i>Journal of Applied Physics</i> , <b>2014</b> , 116, 043103	2.5	4
302	Carrier flow and nonequilibrium superconductivity in superconductor-based LEDs. <i>Applied Physics Express</i> , <b>2014</b> , 7, 073101	2.4	2
301	Symmetric quantum dots as efficient sources of highly entangled photons: Violation of Bell's inequality without spectral and temporal filtering. <i>Physical Review B</i> , <b>2013</b> , 88,	3.3	104
300	Temperature dependent carrier dynamics in telecommunication band InAs quantum dots and dashes grown on InP substrates. <i>Journal of Applied Physics</i> , <b>2013</b> , 113, 033506	2.5	28
299	Single-photon emission in telecommunication band from an InAs quantum dot grown on InP with molecular-beam epitaxy. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 061114	3.4	23
298	Growth and Optimization of 2- $\mu\text{m}$ InGaSb/AlGaSb Quantum-Well-Based VECSELs on GaAs/AlGaAs DBRs. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>2013</b> , 19, 1700611-1700611	3.8	4
297	Metal-coated semiconductor nanostructures and simulation of photon extraction and coupling to optical fibers for a solid-state single-photon source. <i>Nanotechnology</i> , <b>2013</b> , 24, 455205	3.4	13

296	Enhanced light absorption in thin-film solar cells with light propagation direction conversion. <i>Optics Express</i> , <b>2013</b> , 21 Suppl 3, A539-47	3.3	4
295	Carrier dynamics and photoluminescence quenching mechanism of strained InGaSb/AlGaSb quantum wells. <i>Journal of Applied Physics</i> , <b>2013</b> , 113, 053505	2.5	5
294	Enhanced Photon Extraction from a Quantum Dot Induced by a Silver Microcolumnar Photon Reflector. <i>Applied Physics Express</i> , <b>2013</b> , 6, 062801	2.4	14
293	Fiber-Based Bidirectional Solid-State Single-Photon Emitter Based on Semiconductor Quantum Dot. <i>Applied Physics Express</i> , <b>2013</b> , 6, 065203	2.4	9
292	Carrier-transfer dynamics between neutral and charged excitonic states in a single quantum dot probed with second-order photon correlation measurements. <i>Physical Review B</i> , <b>2013</b> , 88,	3.3	8
291	Bright single-photon source based on an InAs quantum dot in a silver-embedded nanocone structure. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 131114	3.4	18
290	High-Q resonance modes observed in a metallic nanocavity. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 191104	3.4	4
289	Spectral and Transient Luminescence Measurements on GaSb/AlGaSb Quantum Wells Grown on GaSb/GaAs Heterojunctions with and without Interfacial Misfit Arrays. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 022101	1.4	
288	Photon-pair generation based on superconductivity. <i>IEICE Electronics Express</i> , <b>2012</b> , 9, 1184-1200	0.5	4
287	Inter-dot coupling and excitation transfer mechanisms of telecommunication band InAs quantum dots at elevated temperatures. <i>New Journal of Physics</i> , <b>2012</b> , 14, 023037	2.9	8
286	Cooper-Pair Radiative Recombination in Semiconductor Heterostructures: Impact on Quantum Optics and Optoelectronics. <i>Japanese Journal of Applied Physics</i> , <b>2012</b> , 51, 010114	1.4	2
285	Silver Embedded Nanomesas as Enhanced Single Quantum Dot Emitters in the Telecommunication C Band. <i>Japanese Journal of Applied Physics</i> , <b>2012</b> , 51, 06FF12	1.4	3
284	Longitudinal and transverse exciton-spin relaxation in a single InAsP quantum dot embedded inside a standing InP nanowire using photoluminescence spectroscopy. <i>Physical Review B</i> , <b>2012</b> , 85,	3.3	5
283	Anomalous dip observed in intensity autocorrelation function as an inherent nature of single-photon emitters. <i>Applied Physics Letters</i> , <b>2012</b> , 101, 161107	3.4	16
282	Cooper-Pair Radiative Recombination in Semiconductor Heterostructures: Impact on Quantum Optics and Optoelectronics. <i>Japanese Journal of Applied Physics</i> , <b>2012</b> , 51, 010114	1.4	3
281	Silver Embedded Nanomesas as Enhanced Single Quantum Dot Emitters in the Telecommunication C Band. <i>Japanese Journal of Applied Physics</i> , <b>2012</b> , 51, 06FF12	1.4	
280	Characterization of two-photon polarization mixed states generated from entangled-classical hybrid photon source. <i>Optics Express</i> , <b>2011</b> , 19, 14249-59	3.3	5
279	Strongly suppressed multi-photon generation from a single quantum dot in a metal-embedded structure. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2011</b> , 8, 337-339		10

278	GaSb quantum rings grown by metal organic molecular beam epitaxy. <i>Journal of Crystal Growth</i> , <b>2011</b> , 323, 233-235	1.6	1
277	Precise slit-width control of niobium apertures for superconducting LEDs. <i>Nanotechnology</i> , <b>2011</b> , 22, 045302	3.4	3
276	Transport properties of Andreev polarons in a superconductor-semiconductor-superconductor junction with superlattice structure. <i>Physical Review Letters</i> , <b>2011</b> , 106, 157002	7.4	5
275	Enhanced photon generation in a Nb/n-InGaAs/p-InP superconductor/semiconductor-diode light emitting device. <i>Physical Review Letters</i> , <b>2011</b> , 107, 157403	7.4	26
274	Conversion of Light Propagation Direction for Highly Efficient Solar Cells. <i>Applied Physics Express</i> , <b>2011</b> , 4, 102301	2.4	3
273	Quantum-Dot-Based Photon Emission and Media Conversion for Quantum Information Applications. <i>Advances in Mathematical Physics</i> , <b>2010</b> , 2010, 1-13	1.1	7
272	Transport characteristics of a superconductor-based LED. <i>Superconductor Science and Technology</i> , <b>2010</b> , 23, 034025	3.1	9
271	Position controlled nanowires for infrared single photon emission. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 171106	3.6	47
270	A Cooper-Pair Light-Emitting Diode: Temperature Dependence of Both Quantum Efficiency and Radiative Recombination Lifetime. <i>Applied Physics Express</i> , <b>2010</b> , 3, 054001	2.4	18
269	Superconducting transport in an LED with Nb electrodes. <i>Physica C: Superconductivity and Its Applications</i> , <b>2010</b> , 470, 814-817	1.3	6
268	First-order photon interference of a single photon from a single quantum dot. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2010</b> , 42, 2536-2539	3	
267	Luminescence of a cooper pair. <i>Physical Review Letters</i> , <b>2009</b> , 103, 187001	7.4	31
266	LO phonon-plasmon coupled modes and carrier mobilities in heavily Se-doped Ga(As, N) thin films. <i>Journal of Materials Science: Materials in Electronics</i> , <b>2009</b> , 20, 425-429	2.1	0
265	Spin-flip quenching in trion state mediated by optical phonons in a single quantum dot. <i>Physica Status Solidi (B): Basic Research</i> , <b>2009</b> , 246, 775-778	1.3	1
264	Improved luminescence efficiency of InAs quantum dots grown on atomic terraced GaAs surface prepared with in-situ chemical etching. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2009</b> , 6, 868-871		1
263	Exciton coherence in clean single InP/InAsP/InP nanowire quantum dots emitting in infra-red measured by Fourier spectroscopy. <i>Journal of Physics: Conference Series</i> , <b>2009</b> , 193, 012132	0.3	9
262	Electron effective mass and mobility in heavily doped n-GaAsN probed by Raman scattering. <i>Journal of Applied Physics</i> , <b>2008</b> , 103, 103528	2.5	14
261	Superconductor-based Light Emitting Diode: Demonstration of Role of Cooper Pairs in Radiative Recombination Processes. <i>Applied Physics Express</i> , <b>2008</b> , 1, 011701	2.4	19

260	Exciton-phonon interactions observed in blue emission band in Te-delta-doped ZnSe. <i>Journal of Applied Physics</i> , <b>2008</b> , 104, 033531	2.5	2
259	Excitonic spin-state preservation mediated by optical-phonon resonant excitation in a single quantum dot. <i>Physical Review B</i> , <b>2008</b> , 78,	3.3	4
258	Differential resistance oscillations with microwave irradiation in a superconductor-semiconductor junction. <i>Journal of Physics: Conference Series</i> , <b>2008</b> , 109, 012033	0.3	4
257	Fourier spectroscopy of decoherence of exciton and their complexes in single InAlAs quantum dots. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2008</b> , 5, 351-355		1
256	Luminescence observed from a junction field-effect transistor with Nb/n-InGaAs/Nb junction. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2008</b> , 5, 2816-2818		5
255	Response to Comment on Luminescence study on evolution from Te isoelectronic centers to type-II ZnTe quantum dots grown by metalorganic molecular-beam epitaxy[J. Crystal Growth 301B02 (2007) 277]. <i>Journal of Crystal Growth</i> , <b>2008</b> , 310, 723	1.6	1
254	Single photon emission with high degree of circular polarization from a single quantum dot under zero magnetic field. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2008</b> , 40, 1824-1827	3	1
253	Highly circular-polarized single photon generation from a single quantum dot at zero magnetic field. <i>Microelectronics Journal</i> , <b>2008</b> , 39, 327-330	1.8	0
252	Role of Cooper pairs for the generation of entangled photon pairs from single quantum dots. <i>Microelectronics Journal</i> , <b>2008</b> , 39, 344-347	1.8	4
251	Fabrication and characterization of a highQmicrodisc laser using InAs quantum dot active regions. <i>Nanotechnology</i> , <b>2007</b> , 18, 055401	3.4	3
250	Fundamental Properties of Wide Bandgap Semiconductors <b>2007</b> , 25-96		
249	Room-temperature stimulated emission from ZnO thin films grown by radio-frequency magnetron sputtering. <i>Journal of Luminescence</i> , <b>2007</b> , 122-123, 825-827	3.8	3
248	Room temperature ultraviolet lasing action in high-quality ZnO thin films. <i>Journal of Luminescence</i> , <b>2007</b> , 122-123, 828-830	3.8	13
247	Luminescence study on evolution from Te isoelectronic centers to type-II ZnTe quantum dots grown by metalorganic molecular-beam epitaxy. <i>Journal of Crystal Growth</i> , <b>2007</b> , 301-302, 277-280	1.6	12
246	Detailed Measurements of Nuclear Spin Polarizations in a Single InAlAs Quantum Dot Through Overhauser Shift of Photoluminescence. <i>Journal of Superconductivity and Novel Magnetism</i> , <b>2007</b> , 20, 447-451	1.5	1
245	Nucleation and Growth Mode of GaN on Vicinal SiC Surfaces. <i>Japanese Journal of Applied Physics</i> , <b>2007</b> , 46, L348-L351	1.4	
244	Novel Nano-Heterostructure Materials and Related Devices <b>2007</b> , 281-327		
243	Role of Nitrogen Precursor Supplies on InAs Quantum Dot Surfaces in Their Emission Wavelengths. <i>Japanese Journal of Applied Physics</i> , <b>2006</b> , 45, L529-L532	1.4	3

242	Anisotropic Lattice Deformation of InAs Self-Assembled Quantum Dots Embedded in GaNAs Strain Compensating Layers. <i>Japanese Journal of Applied Physics</i> , <b>2006</b> , 45, L57-L59	1.4	3
241	Superconductor-Based Quantum-Dot Light-Emitting Diodes: Role of Cooper Pairs in Generating Entangled Photon Pairs. <i>Japanese Journal of Applied Physics</i> , <b>2006</b> , 45, 9264-9271	1.4	31
240	The application of an InGaAs/GaAsN strain-compensated superlattice to InAs quantum dots. <i>Journal of Applied Physics</i> , <b>2006</b> , 99, 103103	2.5	6
239	Intrinsic exciton transitions in high-quality ZnO thin films grown by plasma-enhanced molecular-beam epitaxy on sapphire substrates. <i>Journal of Applied Physics</i> , <b>2006</b> , 99, 063709	2.5	9
238	Formation of CdO dots on atomically flat ZnO surfaces. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2006</b> , 3, 933-937		5
237	Origin of asymmetric splitting of a neutral exciton in a single semiconductor quantum dot. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2006</b> , 3, 3908-3911		
236	Overhauser shift in photoluminescence of excitons with fine structure from a single self-assembled InAlAs quantum dot. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2006</b> , 3, 4372-4375		3
235	Time-resolved photoluminescence in annealed self-assembled InAs quantum dots. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2006</b> , 3, 4299-4302		
234	Triggered single-photon emission and cross-correlation properties in InAlAs quantum dot. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2006</b> , 32, 144-147	3	7
233	Deterministic Single-Photon and Polarization-Correlated Photon Pair Generations From a Single InAlAs Quantum Dot. <i>Journal of Nanoelectronics and Optoelectronics</i> , <b>2006</b> , 1, 39-51	1.3	34
232	Structural and Luminescence Properties of InAs Quantum Dots: Effect of Nitrogen Exposure on Dot Surfaces. <i>Japanese Journal of Applied Physics</i> , <b>2005</b> , 44, L1512-L1515	1.4	6
231	Theory of strain states in InAs quantum dots and dependence on their capping layers. <i>Journal of Applied Physics</i> , <b>2005</b> , 98, 063502	2.5	19
230	MOMBE Growth and Characterization of III-V-N Compounds and Application to InAs Quantum Dots <b>2005</b> , 137-155		
229	Single-photon generation from InAlAs single quantum dot. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2005</b> , 2, 3833-3837		4
228	Dynamic nuclear polarization in a self-assembled InAlAs quantum dot. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2005</b> , 2, 3838-3842		2
227	Photon Antibunching Observed from an InAlAs Single Quantum Dot. <i>Japanese Journal of Applied Physics</i> , <b>2005</b> , 44, L793-L796	1.4	21
226	Nucleation Stages of Carbon Nanotubes on SiC(0001) by Surface Decomposition. <i>Japanese Journal of Applied Physics</i> , <b>2005</b> , 44, L803-L805	1.4	12
225	Photon-spin qubit-conversion based on Overhauser shift of Zeeman energies in quantum dots. <i>Applied Physics Letters</i> , <b>2005</b> , 87, 112506	3.4	23

224	Surface-emitting stimulated emission in high-quality ZnO thin films. <i>Journal of Applied Physics</i> , <b>2004</b> , 96, 3733-3736	2.5	30
223	SiC Surface Nanostructures Induced by Self-Ordering of Nano-Facets. <i>Materials Science Forum</i> , <b>2004</b> , 457-460, 407-410	0.4	1
222	Optical properties of GaAsNSe/GaAs superlattice investigated by means of piezoelectric photothermal spectroscopy for nonradiative electron transitions. <i>IEE Proceedings: Optoelectronics</i> , <b>2004</b> , 151, 328-330		
221	Dynamical properties of atom-like emissions from single localized states in ZnCdS ternary mesa-shaped structures. <i>Physica Status Solidi (B): Basic Research</i> , <b>2004</b> , 241, 503-506	1.3	
220	Formation of ohmic contacts to p-type ZnO. <i>Physica Status Solidi (B): Basic Research</i> , <b>2004</b> , 241, 635-639	1.3	10
219	Epitaxial ZnO growth and p-type doping with MOMBE. <i>Physica Status Solidi (B): Basic Research</i> , <b>2004</b> , 241, 640-647	1.3	23
218	Study of optimal coupling of ZnS pyramidal microcavities with distributed Bragg reflectors. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2004</b> , 1, 1034-1037		
217	Observation of reflection high-energy electron diffraction oscillation during MOMBE growth of AlAs and related modulated semiconductor structures. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2004</b> , 21, 756-760	3	1
216	Observation of clear negative differential resistance characteristics in GaAsNSe/GaAs and GaAsNSb/GaAs multiple quantum wells at room temperature. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2004</b> , 21, 727-731	3	4
215	GaNAs as Strain Compensating Layer for 1.55 $\mu$ m Light Emission from InAs Quantum Dots. <i>Japanese Journal of Applied Physics</i> , <b>2003</b> , 42, 5598-5601	1.4	18
214	III-V-related quantum structures for 1.5 [ $\mu$ m] emission. <i>IEE Proceedings: Optoelectronics</i> , <b>2003</b> , 150, 52		
213	III-V quantum dots grown by MOVPE. <i>Journal of Crystal Growth</i> , <b>2003</b> , 248, 301-309	1.6	9
212	Structural properties of CdO layers grown on GaAs (001) substrates by metalorganic molecular beam epitaxy. <i>Journal of Crystal Growth</i> , <b>2003</b> , 252, 219-225	1.6	3
211	Emissions from single localized states observed in ZnCdS ternary alloy mesa structures. <i>Applied Physics Letters</i> , <b>2003</b> , 82, 4277-4279	3.4	4
210	Improvement of InAs quantum-dot optical properties by strain compensation with GaNAs capping layers. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 4524-4526	3.4	25
209	1.55 $\mu$ m emission from GaInNAs with indium-induced increase of N concentration. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 1992-1994	3.4	11
208	Observation of reflection high-energy electron diffraction oscillation during metalorganic-molecular-beam epitaxy of AlAs and control of carbon incorporation. <i>Journal of Applied Physics</i> , <b>2003</b> , 94, 4871	2.5	5
207	Structural anisotropy in GaN films grown on vicinal 4H-SiC surfaces by metallorganic molecular-beam epitaxy. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 1569-1571	3.4	11

206	Self-ordering of nanofacets on vicinal SiC surfaces. <i>Physical Review Letters</i> , <b>2003</b> , 91, 226107	7.4	81
205	Metalorganic molecular-beam epitaxy and characterization of GaAsNSe/GaAs superlattices emitting around 1.5- $\mu$ m-wavelength region. <i>Applied Physics Letters</i> , <b>2003</b> , 82, 898-900	3.4	6
204	Longitudinal-Optical-Phonon-Assisted Resonant Excitations of CdS Quantum Dots Embedded in ZnSe/(ZnSe/MgS Superlattice) Microcavities. <i>Physica Status Solidi (B): Basic Research</i> , <b>2002</b> , 229, 961-969	1.3	3
203	Study of Resonance Wavelengths in II-VI Semiconductor Photonic Dots: Pyramidal Size Dependences and Luminescence Properties. <i>Physica Status Solidi (B): Basic Research</i> , <b>2002</b> , 229, 971-976	1.3	8
202	Growth Activation of ZnO Layers with H <sub>2</sub> O Vapor on a-Face of Sapphire Substrate by Metalorganic Molecular-Beam Epitaxy. <i>Physica Status Solidi A</i> , <b>2002</b> , 192, 224-229		6
201	Strong coupling of CdS quantum dots to confined photonic modes in ZnSe-based microcavities. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2002</b> , 13, 403-407	3	2
200	Modified spontaneous emission properties of CdS quantum dots embedded in novel three-dimensional microcavities. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2002</b> , 13, 441-445	2.5	3
199	CdO epitaxial layers grown on (0 0 1) GaAs surfaces by metalorganic molecular-beam epitaxy. <i>Journal of Crystal Growth</i> , <b>2002</b> , 237-239, 518-522	1.6	14
198	Erbium-doped GaP grown by MOMBE and their optical properties. <i>Journal of Crystal Growth</i> , <b>2002</b> , 237-239, 1423-1427	1.6	
197	Longitudinal-optical-phonon-assisted energy relaxation in self-assembled CdS quantum dots embedded in ZnSe. <i>Journal of Applied Physics</i> , <b>2002</b> , 92, 3573-3578	2.5	3
196	Photoluminescence study of InAs quantum dots embedded in GaNAs strain compensating layer grown by metalorganic-molecular-beam epitaxy. <i>Journal of Applied Physics</i> , <b>2002</b> , 92, 6813-6818	2.5	28
195	H <sub>2</sub> O-Vapor-Activated ZnO Growth on a-Face Sapphire Substrates by Metalorganic Molecular-Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>2002</b> , 41, 2851-2854	1.4	19
194	Growth and structural characterization of III-IV semiconductor alloys. <i>Semiconductor Science and Technology</i> , <b>2002</b> , 17, 755-761	1.8	33
193	Nitrogen-Doped p-Type ZnO Layers Prepared with H <sub>2</sub> O Vapor-Assisted Metalorganic Molecular-Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>2002</b> , 41, L1281-L1284	1.4	115
192	Structural properties of GaAsN grown on (001) GaAs by metalorganic molecular beam epitaxy. <i>Journal of Electronic Materials</i> , <b>2001</b> , 30, 900-906	1.9	3
191	RADIATIVE EFFICIENCY OF LOCALIZED EXCITONS IN ZnCdS TERNARY ALLOYS. <i>International Journal of Modern Physics B</i> , <b>2001</b> , 15, 3718-3721	1.1	3
190	Highly conductive GaAsNSe alloys grown on GaAs and their nonalloyed ohmic properties. <i>Applied Physics Letters</i> , <b>2001</b> , 79, 3284-3286	3.4	19
189	Nucleation and growth kinetics of AlN films on atomically smooth 6H-SiC (0001) surfaces. <i>Applied Physics Letters</i> , <b>2001</b> , 78, 3612-3614	3.4	38



188	Single-crystalline rocksalt CdO layers grown on GaAs (001) substrates by metalorganic molecular-beam epitaxy. <i>Applied Physics Letters</i> , <b>2001</b> , 79, 470-472	3.4	26
187	Luminescence properties of CdS quantum dots embedded in monolithic II-VI microcavity. <i>Springer Proceedings in Physics</i> , <b>2001</b> , 675-676	0.2	
186	New type of ZnCdS/ZnMgCdS heterostructures lattice-matched to GaAs for selective-area growth. <i>Journal of Crystal Growth</i> , <b>2000</b> , 214-215, 125-129	1.6	1
185	Luminescence properties of ZnO films grown on GaAs substrates by molecular-beam epitaxy excited by electron cyclotron resonance oxygen plasma. <i>Journal of Crystal Growth</i> , <b>2000</b> , 214-215, 280-283 <sup>16</sup>	1.6	42
184	Periodic doping of GaAs : Zn p-type nano-clusters in ZnSe grown by metalorganic molecular-beam epitaxy. <i>Journal of Crystal Growth</i> , <b>2000</b> , 214-215, 524-528	1.6	2
183	Study of site change of Li impurities in ZnSe by co-doping with iodine. <i>Journal of Crystal Growth</i> , <b>2000</b> , 214-215, 562-566	1.6	7
182	MOVPE growth of ZnSe/ZnMgS distributed Bragg reflectors with high refractive-index contrast. <i>Journal of Crystal Growth</i> , <b>2000</b> , 214-215, 1019-1023	1.6	8
181	Enhancement of spontaneous emission by ZnS-based II-VI semiconductor photonic dots. <i>Journal of Crystal Growth</i> , <b>2000</b> , 214-215, 1024-1028	1.6	1
180	Growth mechanism of selectively grown II-VI semiconductor photonic dots for short-wavelength light emitters. <i>Journal of Crystal Growth</i> , <b>2000</b> , 221, 425-430	1.6	8
179	Role of ZnS buffer layers in growth of zincblende ZnO on GaAs substrates by metalorganic molecular-beam epitaxy. <i>Journal of Crystal Growth</i> , <b>2000</b> , 221, 435-439	1.6	38
178	Formation of wire-like surfaces and lateral composition modulation in GaAsN grown by metalorganic molecular-beam epitaxy. <i>Journal of Crystal Growth</i> , <b>2000</b> , 221, 546-550	1.6	12
177	Microcavities with distributed Bragg reflectors based on ZnSe/MgS superlattice grown by MOVPE. <i>Journal of Crystal Growth</i> , <b>2000</b> , 221, 699-703	1.6	24
176	Investigations of optical and electrical properties of In-doped GaN films grown by gas-source molecular beam epitaxy. <i>Journal of Crystal Growth</i> , <b>2000</b> , 209, 396-400	1.6	7
175	Fabrication of selectively grown II-VI widegap semiconductor photonic dots on (001)GaAs with MOMBE. <i>Journal of Crystal Growth</i> , <b>2000</b> , 209, 518-521	1.6	3
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173	Intrinsic and Extrinsic Excitonic Features in MgS/ZnSe Superlattices Revealed by Microspectroscopy. <i>Japanese Journal of Applied Physics</i> , <b>2000</b> , 39, 501-504	1.4	2
172	Atomic force microscope based patterning of carbonaceous masks for selective area growth on semiconductor surfaces. <i>Journal of Applied Physics</i> , <b>2000</b> , 88, 3158-3165	2.5	12
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165	Growth and luminescence properties of self-organized ZnSe quantum dots. <i>Applied Physics Letters</i> , <b>1999</b> , 75, 235-237	3.4	42
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161	Reexamination of N composition dependence of coherently grown GaNAs band gap energy with high-resolution x-ray diffraction mapping measurements. <i>Applied Physics Letters</i> , <b>1999</b> , 74, 1254-1256	3.4	221
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157	MOVPE growth of ZnSe/ZnS distributed Bragg reflectors on GaAs (1 0 0) and (3 1 1)B substrates. <i>Journal of Crystal Growth</i> , <b>1998</b> , 184-185, 777-782	1.6	8
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149	Atomic Force Microscope Nanolithography on SiO <sub>2</sub> /Semiconductor Surfaces. <i>Japanese Journal of Applied Physics</i> , <b>1997</b> , 36, 4057-4060	1.4	12
148	Luminescence of Excitons Localized by Monolayer Interface Fluctuations in ZnSe/MgS Superlattices Grown by Metalorganic Vapor Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>1997</b> , 36, 4199-4203	1.4	8
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145	Excitonic properties of zinc-blende ZnSe/MgS superlattices studied by reflection spectroscopy. <i>Physical Review B</i> , <b>1997</b> , 55, 4449-4455	3.3	17
144	Excitonic luminescence up to room temperature in a ZnSe/MgS superlattice. <i>Applied Physics Letters</i> , <b>1997</b> , 70, 2350-2352	3.4	16
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141	Growth of zincblende MgSZnSe superlattices and their heterointerface properties. <i>Journal of Crystal Growth</i> , <b>1997</b> , 170, 480-484	1.6	5
140	Atomic force microscopy study of ZnSeGaAs heteroepitaxy processes by metalorganic vapour phase epitaxy. <i>Applied Surface Science</i> , <b>1997</b> , 113-114, 371-376	6.7	4
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136	Purge Effect on Heterointerfaces of ZnSe/MgS Superlattices Grown by Metalorganic Vapor Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>1996</b> , 35, L1658-L1661	1.4	4
135	Epitaxial growth of zinc-blende ZnSe/MgS superlattices on (001) GaAs. <i>Applied Physics Letters</i> , <b>1996</b> , 68, 844-846	3.4	41

134	Three-photon absorption coefficients in ZnSe/ZnS <sub>0.18</sub> Se <sub>0.82</sub> strained-layer superlattices. <i>Nuovo Cimento Della Societa Italiana Di Fisica D - Condensed Matter, Atomic, Molecular and Chemical Physics, Biophysics</i> , <b>1996</b> , 18, 465-469		1
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132	Time-resolved study of stimulated emission in superlattices. <i>Journal of Crystal Growth</i> , <b>1996</b> , 159, 657-660		3
131	Lasing in ZnSe/ZnS <sub>0.18</sub> Se <sub>0.82</sub> superlattices. <i>Physical Review B</i> , <b>1996</b> , 54, 17812-17818	3.3	4
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120	Study of mechanism to control electrical properties of AlAs grown using amine-alane with metalorganic molecular-beam epitaxy. <i>Applied Physics Letters</i> , <b>1994</b> , 64, 1549-1551	3.4	3
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118	One- and two-phonon scattering processes in ZnSe/ZnS <sub>x</sub> Se <sub>1-x</sub> superlattices studied by micro-Raman spectroscopy. <i>Physical Review B</i> , <b>1994</b> , 50, 4988-4991	3.3	1
117	Pressure-induced conduction-band crossover in a ZnSe/ZnS <sub>0.18</sub> Se <sub>0.82</sub> symmetric superlattice. <i>Physical Review B</i> , <b>1994</b> , 50, 14635-14638	3.3	9

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95	Photoirradiation Effect on Photoluminescence from Anodized Porous Silicons and Luminescence Mechanism. <i>Japanese Journal of Applied Physics</i> , <b>1992</b> , 31, L494-L497	1.4	43
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61	. <i>IEEE Photonics Technology Letters</i> , <b>1990</b> , 2, 546-548	2.2	7
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34	Mode characteristics of the multiple-stripe laser effects of the loss embedded in the outer unpumped region. <i>Journal of Lightwave Technology</i> , <b>1986</b> , 4, 730-738	4	2
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26	Size effect modulation light sources [Possibility of LED mode operation at room temperature. <i>Superlattices and Microstructures</i> , <b>1985</b> , 1, 335-337	2.8	12
25	Quenching of photoluminescence from GaAs/AlGaAs single quantum well by an electric field at high temperature. <i>Superlattices and Microstructures</i> , <b>1985</b> , 1, 111-113	2.8	12
24	Analysis of transverse modes of phase-locked multi-stripe lasers. <i>Electronics Letters</i> , <b>1985</b> , 21, 713	1.1	9
23	Electric Field Effect on Subband State Transitions Peaks in the Photoluminescence from a GaAlAs Quantum Well Structure. <i>Japanese Journal of Applied Physics</i> , <b>1985</b> , 24, L589-L592	1.4	12
22	Noncontact photoacoustic measurements of semiconductors with Michelson interferometry. <i>Journal of Applied Physics</i> , <b>1985</b> , 58, 615-617	2.5	25
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20	Transient Response of Photoluminescence for Electric Field in a GaAs/Al <sub>0.7</sub> Ga <sub>0.3</sub> As Single Quantum Well: Evidence for Field-Induced Increase in Carrier Life Time. <i>Japanese Journal of Applied Physics</i> , <b>1985</b> , 24, L586-L588	1.4	21
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18	Phase-locked, index-guided multiple-stripe lasers with large refractive index differences. <i>Applied Physics Letters</i> , <b>1984</b> , 45, 1011-1013	3.4	6
17	Spectral hole burnings at high energy tails in spontaneous emission and hot carrier relaxation in InGaAsP lasers. <i>IEEE Journal of Quantum Electronics</i> , <b>1983</b> , 19, 924-929	2	10
16	Quantum Mechanical Size Effect Modulation Light Sources -- A New Field Effect Semiconductor Laser or Light Emitting Device. <i>Japanese Journal of Applied Physics</i> , <b>1983</b> , 22, L22-L24	1.4	66
15	Semiconductor light sources with capabilities of electronic beam-scanning. <i>Electronics Letters</i> , <b>1983</b> , 19, 1002	1.1	6
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12	Hole-Burnings Observed at High Energy Tails in Spontaneous Emission Spectra from 1.3 $\mu\text{m}$ -InGaAsP/InP Lasers. <i>Japanese Journal of Applied Physics</i> , <b>1982</b> , 21, L240-L242	1.4	9
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4	OBSERVATION OF ACOUSTIC EMISSION FROM a-Si : H PIN JUNCTIONS. <i>Journal De Physique Colloque</i> , <b>1981</b> , 42, C4-447-C4-450		2
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